

/ Descriptions

TO-252 b c c d e f MOS g h 4 i _
N-CHANNEL MOSFET in a TO-252 Plastic Package.

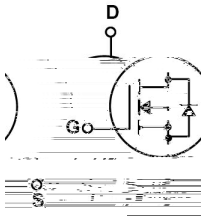
/ Features

j k l N m n o V p N > ? @ A B C D E F G N q r 9 : _
Low On-Resistance, fast switching, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

s t u v i w x i y _ z { | } s t u ~ € , f N I J 7 8 4 5 i K L F G _
Power Management in DC/DC Converter. For LED Backlight DC-DC Boost Converter Solution, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN 1 ^ G

PIN 2 ^ D

PIN 3 ^ S

PIN 4 ^ D

/ Marking

, O P ... † _

See Marking Instructions.

| Parameter | | Symbol | Rating | Unit |
|---|--------------|-----------------------|------------|--------------|
| Drain-Source Voltage | | V_{DS} | 100 | V |
| Drain Current | | $I_D(T_C=25^\circ C)$ | 12 | A |
| Drain Current - Pulsed | | I_{DM} | 28 | A |
| Gate-Source Voltage | | V_{GS} | ± 20 | V |
| Single Pulsed Avalanche Energy | | E_{AS} | 35 | mJ |
| Avalanche Current | | I_{AS} | 2.1 | A |
| Power Dissipation | | $P_D(T_C=25^\circ C)$ | 21.5 | W |
| Operating and Storage Temperature Range | | T_J, T_{stg} | -55 to 150 | $^\circ C$ |
| Junction-to-Ambient | $t \leq 10$ | R_{JA} | 20 | $^\circ C/W$ |
| Junction-to-Ambient | Steady-State | | 50 | |
| Junction-to-Case | Steady-State | R_{JC} | 5.8 | |

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------------------------------|--------------|--------------------------------|-----|-----|-----------|---------|
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V$ $I_D=250\mu A$ | 100 | 106 | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=100V$ $V_{GS}=0V$ | | | 1 | μA |
| Gate-Body Leakage Current Forward | I_{GSS} | $V_{GS}=\pm 20V$ $V_{DS}=0V$ | | | ± 0.1 | μA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$ $I_D=250\mu A$ | 1.0 | 1.8 | 3.0 | V |

BRC850N10SDPQ

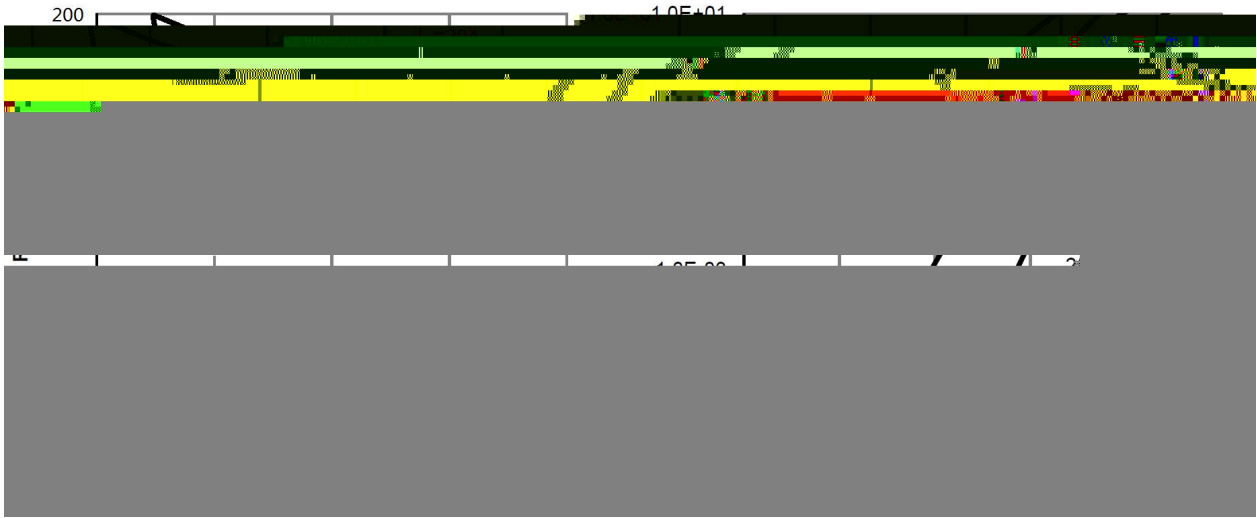
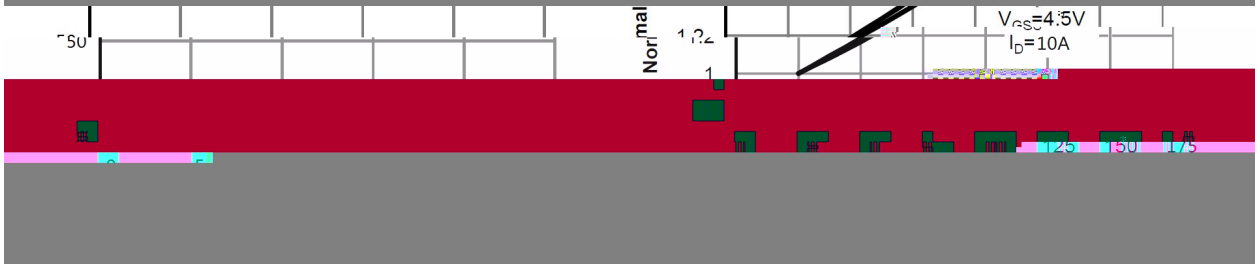
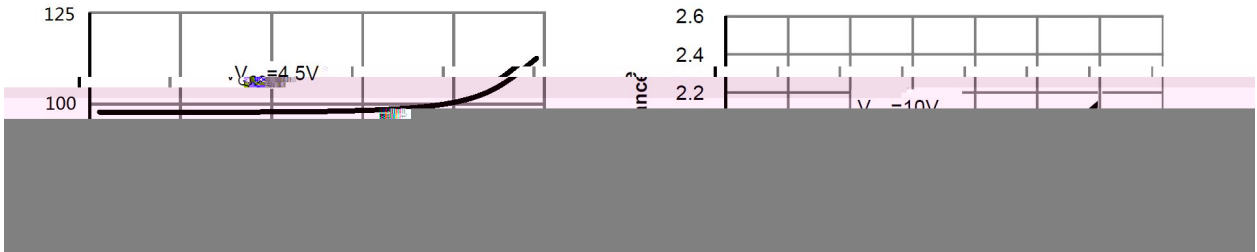
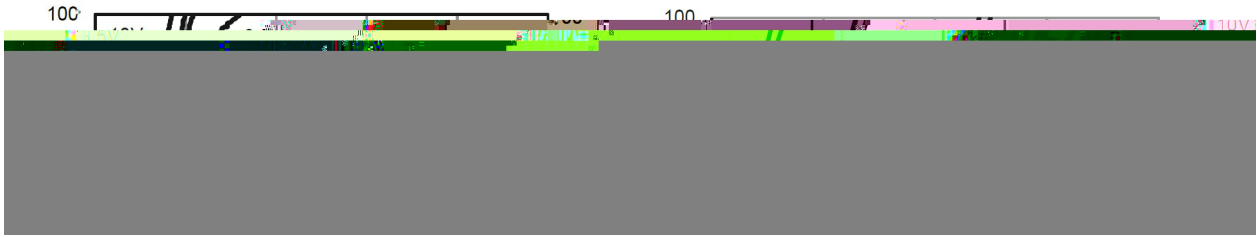
Rev.A Aug.-2022



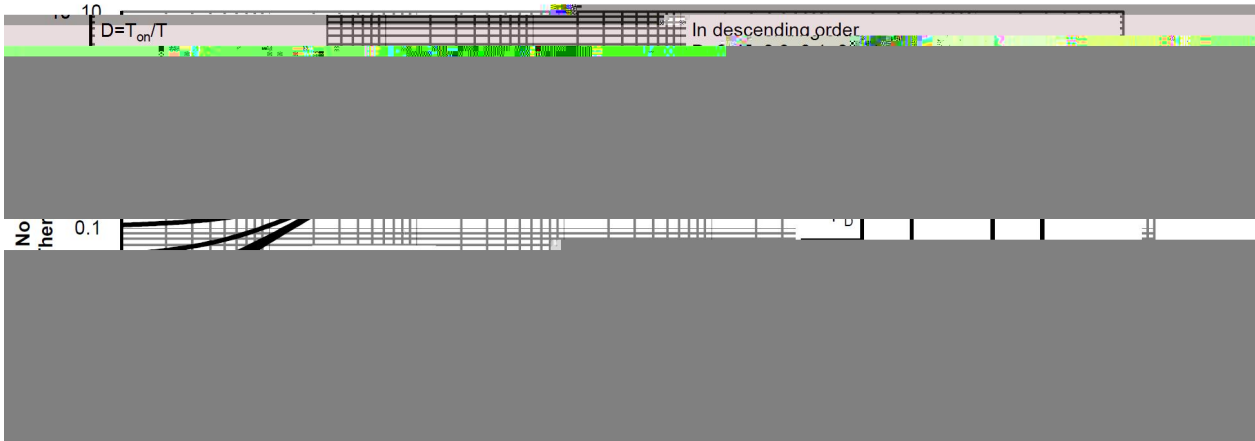
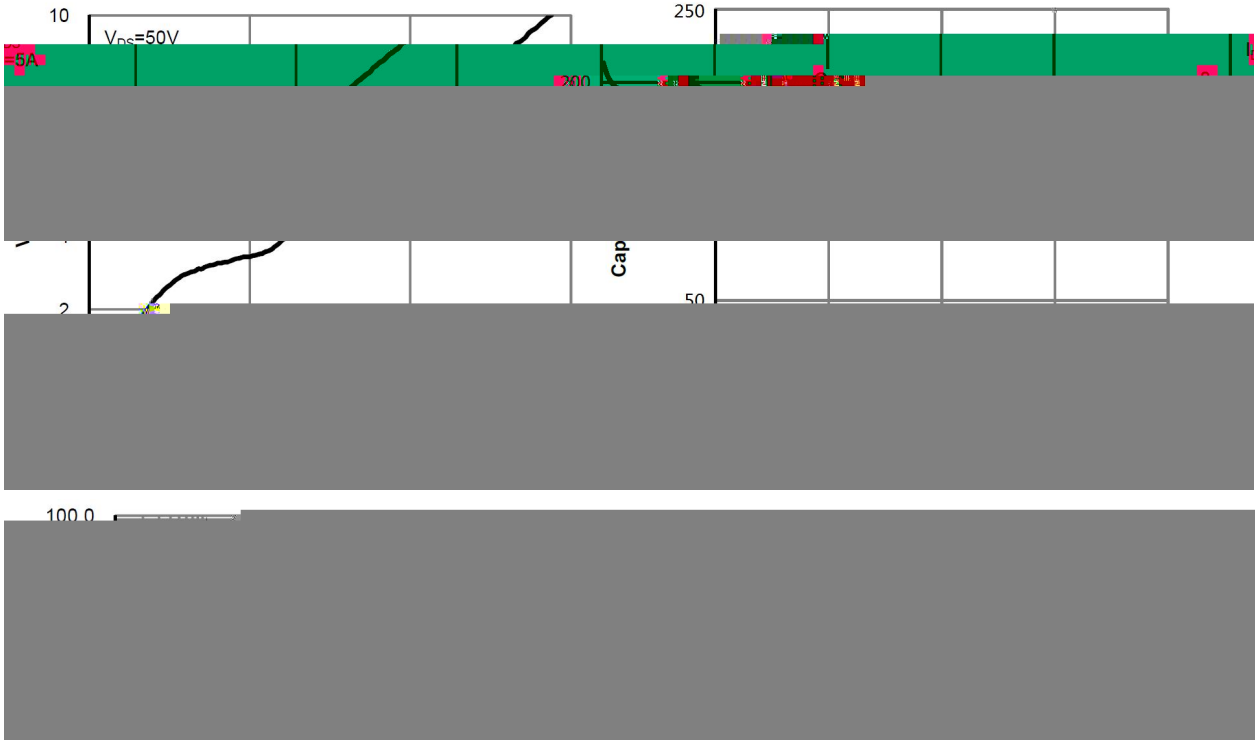
DATA SHEET

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-------------------|---------|-----------------|-----|-----|-----|------|
| Total Gate Charge | $Q_{g($ | $g($ | | | | |

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



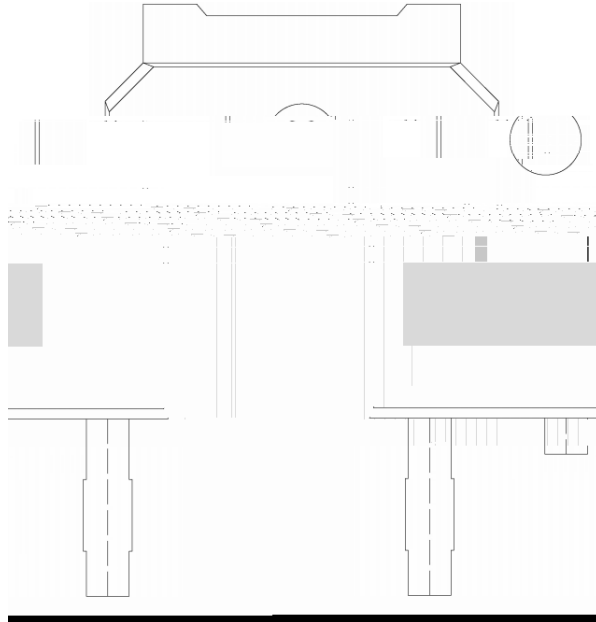
BRCS850N10SDPQ

Rev.A Aug.-2022

DATA SHEET

<http://>

/ Marking Instructa





() / Temperature Profile for IR Reflow Soldering(Pb-Free)

| |
|--|
| |
| |
| |
| |
| |
| |
| |

Note:

- 1 150 200 60 120sec; 1.Preheating:150~200 , Time:60~120sec.
- 2 255±5 5±0.5sec; 2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

| Package Type 封装形式 | Units 包装数量 | | | | | 包装尺寸 (unit: mm ³) | | |
|----------------------|--------------------|-------------------------|------------------------|------------------------------|------------------------|-------------------------------|-------------|-------------|
| | Units/Reel 只/卷盘 | Reels/Inner Box 卷盘/盒 | Units/Inner Box 只/盒 | Inner Boxes/Outer Box 盒/箱 | Units/Outer Box 只/箱 | Reel | Inner Box 盒 | Outer Box 箱 |
| TO-252 | 2,500 | 2 | 5,000 | 6 | 30,000 | 13" ×16 | 360×360×50 | 380×335×366 |